HAMAMATSU

PHOTOMULTIPLIER TUBE R7517

High QE, Bialkali Photocathode
28 mm (1-1/8 Inch) Diameter, 9-Stage, Side-On Type

FEATURES

- **Wide Spectral Response ..... 185 nm to 760 nm**
- **High Cathode Sensitivity**
  - **Luminous ..... 160 μA/lm Typ.**
  - **Radiant at 420 nm ..... 105 mA/W Typ.**
  - **Quantum Efficiency at 220 nm ..... 40 % Typ.**
- **High Anode Sensitivity (at 1000 V)**
  - **Luminous ..... 1600 A/lm Typ.**
  - **Radiant at 420 nm ..... 10.5×10^5 A/W Typ.**

APPLICATIONS

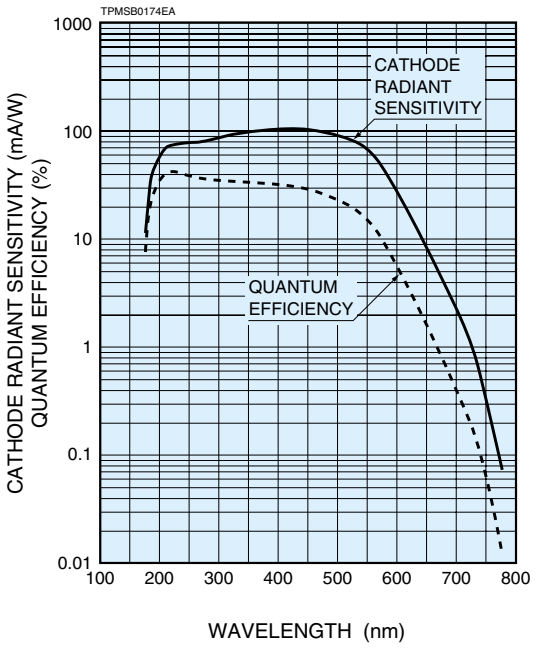
- **Fluorescence Spectrophotometers**
- **Fluorescence Immuno Assay**
- **SO_2 Monitor (UV Fluorescence)**

SPECIFICATIONS

GENERAL

Parameter		Description/Value	Unit
Spectral Response		185 to 760	nm
Wavelength of Maximum Response		420	nm
Photocathode	Material	Bialkali	—
	Minimum Effective Area	8 × 24	mm
Window Material		UV glass	—
Dynode	Secondary Emitting Surface	Bialkali	—
	Structure	Circular-cage	—
	Number of Stages	9	—
Direct Interelectrode Capacitances	Anode to Last Dynode	4	pF
	Anode to All Other Electrodes	6	pF
Base		11-pin base JEDEC No. B11-88	—
Weight		Approx. 45	g
Operating Ambient Temperature		-30 to +50	°C
Storage Temperature		-30 to +50	°C
Suitable Socket		E678–11A (Sold Separately)	—
Suitable Socket Assembly		E717–63 (Sold Separately)	—
		E717–74 (Sold Separately)	

Figure 1: Typical Spectral Response



MAXIMUM RATINGS (Absolute Maximum Values)

Parameter		Value	Unit
Supply Voltage	Between Anode and Cathode	1250	V
	Between Anode and Last Dynode	250	V
Average Anode Current [A]		0.1	mA

CHARACTERISTICS (at 25 °C)

Parameter			Min.	Typ.	Max.	Unit
Cathode Sensitivity	Quantum Efficiency (at Peak Wavelength)		—	40 (at 220 nm)	—	%
	Luminous [B]		150	160	—	μA/lm
	Radiant	at 210 nm	—	71	—	mA/W
		at 420 nm	—	105	—	mA/W
	Red/White Ratio [C]		—	0.01	—	—
	Blue Sensitivity Index [D]		12	13	—	—
Anode Sensitivity	Luminous [E]		1200	1600	—	A/lm
	Radiant	at 210 nm	—	7.1×10^5	—	A/W
		at 420 nm	—	10.5×10^5	—	A/W
Gain [E]			—	1.0×10^7	—	—
Anode Dark Current [F] (After 30 min Storage in Darkness)			—	5	50	nA
ENI (Equivalent Noise Input) [G]			—	1.2×10^{-16}	—	W
Time Response [E]	Anode Pulse Rise Time [H]		—	2.2	—	ns
	Electron Transit Time [I]		—	22	—	ns
	Transit Time Spread (TTS) [J]		—	1.2	—	ns
Anode Current Stability [K]	Light Hysteresis		—	0.1	—	%
	Voltage Hysteresis		—	1.0	—	%

NOTES

A: Averaged over any interval of 30 seconds maximum.

B: The light source is a tungsten filament lamp operated at a distribution temperature of 2856K. Supply voltage is 100 V between the cathode and all other electrodes connected together as anode.

C: Red/White ratio is the quotient of the cathode current measured using a red filter (Toshiba R-68) interposed between the light source and the tube by the cathode current measured with the filter removed under the same conditions as Note B.

D: The value is cathode output current when a blue filter (Corning CS 5-58 polished to 1/2 stock thickness) is interposed between the light source and the tube under the same condition as Note B.

E: Measured with the same light source as Note B and with the voltage distribution ratio shown in Table 1 below.

Table 1: Voltage Distribution Ratio

Electrode	K	Dy1	Dy2	Dy3	Dy4	Dy5	Dy6	Dy7	Dy8	Dy9	P
Distribution Ratio	1	1	1	1	1	1	1	1	1	1	

Supply Voltage: 1000 V, K: Cathode, Dy: Dynode, P: Anode

F: Measured with the same supply voltage and voltage distribution ratio as Note E after removal of light.

G: ENI is an indication of the photon-limited signal-to-noise ratio. It refers to the amount of light in watts to produce a signal-to-noise ratio of unity in the output of a photomultiplier tube.

$$ENI = \frac{\sqrt{2q \cdot Idb \cdot G \cdot \Delta f}}{S}$$

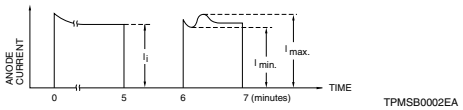
where q = Electronic charge (1.60×10^{-19} coulomb).
Idb = Anode dark current (after 30 minute storage) in amperes.
G = Gain.
Δf = Bandwidth of the system in hertz. 1 hertz is used.
S = Anode radiant sensitivity in amperes per watt at the wavelength of peak response.

H: The rise time is the time for the output pulse to rise from 10 % to 90 % of the peak amplitude when the entire photocathode is illuminated by a delta function light pulse.

I: The electron transit time is the interval between the arrival of delta function light pulse at the entrance window of the tube and the time when the anode output reaches the peak amplitude. In measurement, the whole photocathode is illuminated.

J: Also called transit time jitter. This is the fluctuation in electron transit time between individual pulses in the signal photoelectron mode, and may be defined as the FWHM of the frequency distribution of electron transit times.

K: Hysteresis is temporary instability in anode current after light and voltage are applied.



$$\text{Hysteresis} = \frac{I_{max.} - I_{min.}}{I_i} \times 100\ (\%)$$

(1) Light Hysteresis
The tube is operated at 750 V with an anode current of 1 μA for 5 minutes. The light is then removed from the tube for a minute. The tube is then re-illuminated by the previous light level for a minute to measure the variation.

(2) Voltage Hysteresis
The tube is operated at 300 V with an anode current of 0.1 μA for 5 minutes. The light is then removed from the tube and the supply voltage is quickly increased to 800 V. After a minute, the supply voltage is then reduced to the previous value and the tube is re-illuminated for a minute to measure the variation.

Figure 2: Anode Luminous Sensitivity and Gain Characteristics

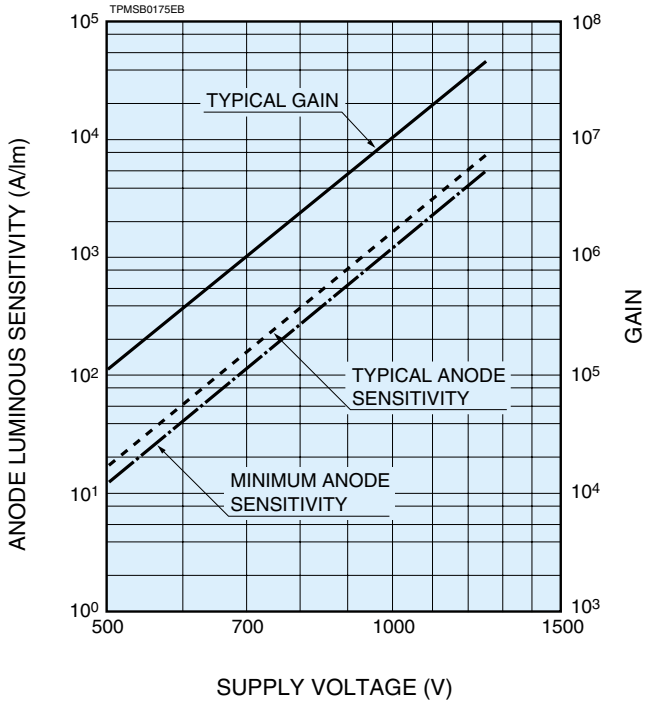


Figure 3: Typical Time Response

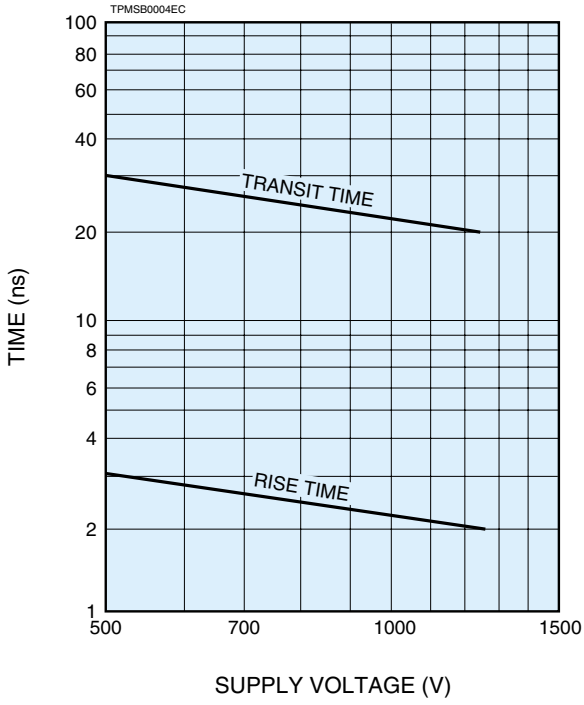


Figure 4: Typical ENI with Wavelength

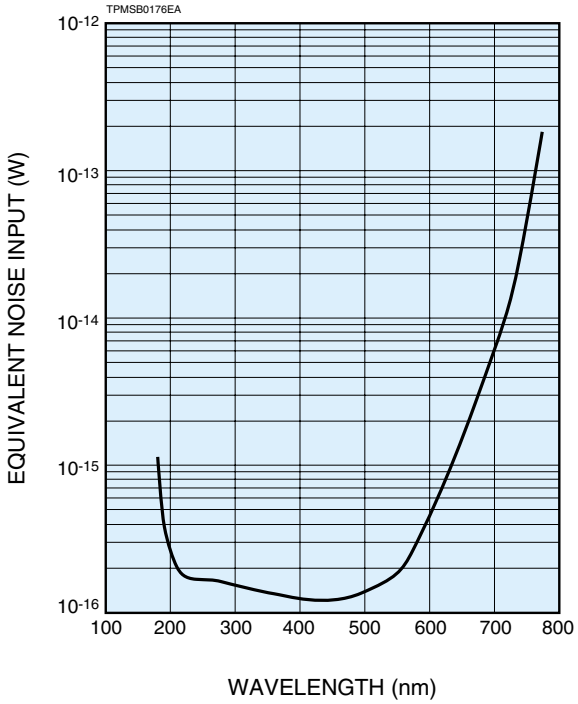


Figure 5: Dimensional Outline and Basing Diagram (Unit: mm)

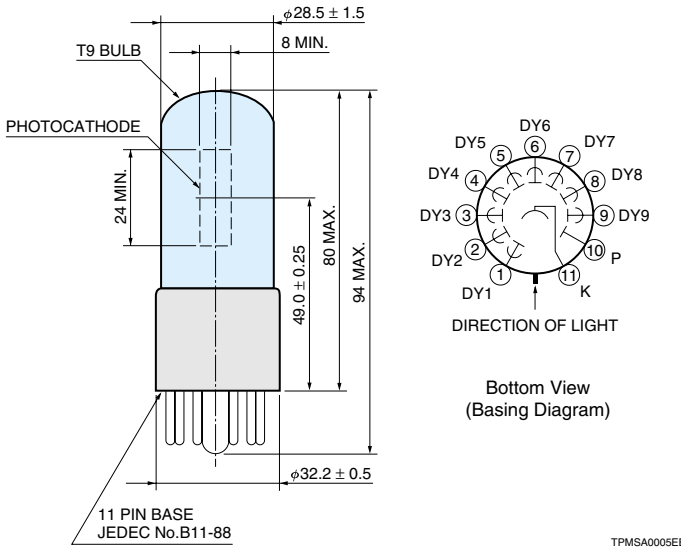


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Figure 6: Socket (Unit: mm) Sold Separately

E678-11A

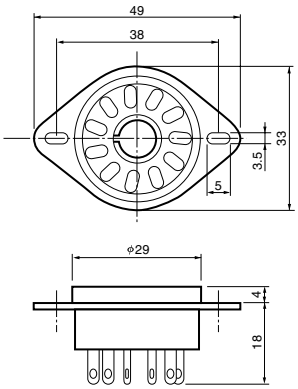

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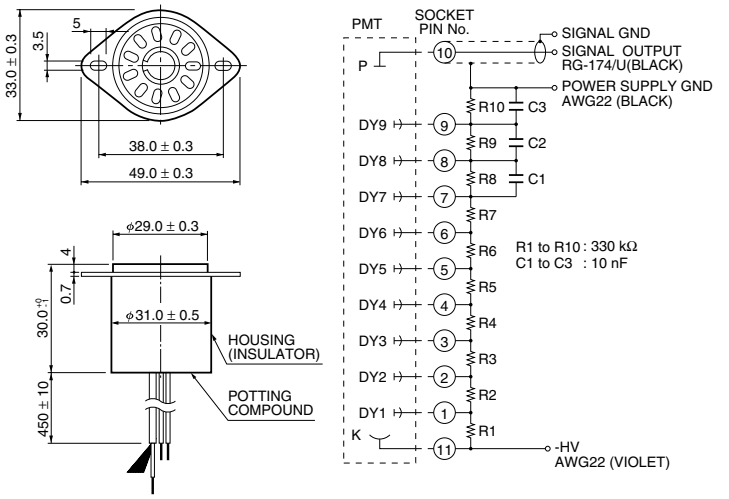
Figure 7: D Type Socket Assembly (Unit: mm) Sold Separately

E717-63



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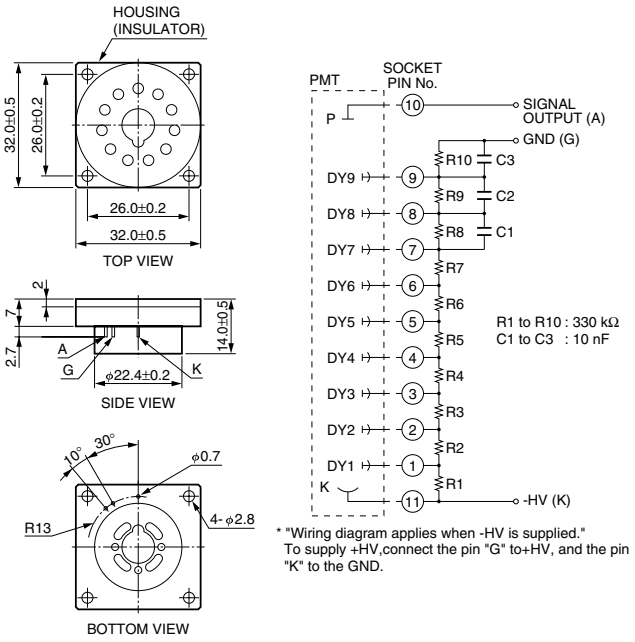
E717-74



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* Hamamatsu also provides C4900 series compact high voltage power supplies and C6270 series DP type socket assemblies which incorporate a DC to DC converter type high voltage power supply.

Warning–Personal Safety Hazards

Electrical Shock–Operating voltages applied to this device present a shock hazard.

HAMAMATSU WEB SITE www.hamamatsu.com

HAMAMATSU PHOTONICS K.K., Electron Tube Division
314-5, Shimokanzo, Iwata City, Shizuoka Pref., 438-0193, Japan, Telephone: (81)539/62-5248, Fax: (81)539/62-2205

U.S.A.: Hamamatsu Corporation: 360 Foothill Road, P. O. Box 6910, Bridgewater. N.J. 08807-0910, U.S.A., Telephone: (1)908-231-0960, Fax: (1)908-231-1218 E-mail: usa@hamamatsu.com
Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49)8152-375-0, Fax: (49)8152-2658 E-mail: info@hamamatsu.de
France: Hamamatsu Photonics France S.A.R.L.: 19, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: (33)1 69 53 71 00, Fax: (33)1 69 53 71 10 E-mail: infos@hamamatsu.fr
United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road Welwyn Garden City Hertfordshire AL7 1BW, United Kingdom, Telephone: 44-(0)1707-294888, Fax: 44(0)1707-325777 E-mail: info@hamamatsu.co.uk
North Europe: Hamamatsu Photonics Norden AB: Smidesvägen 12, SE-171-41 SOLNA, Sweden, Telephone: (46)8-509-031-00, Fax: (46)8-509-031-01 E-mail: info@hamamatsu.se
Italy: Hamamatsu Photonics Italia: S.R.L.: Strada della Moia, 1/E, 20020 Arese, (Milano), Italy, Telephone: (39)02-935 81 733, Fax: (39)02-935 81 741 E-mail: info@hamamatsu.it

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